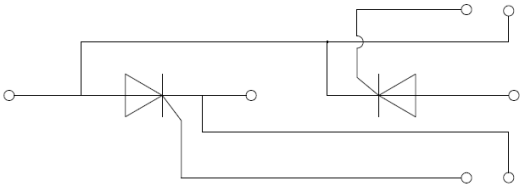
"

0

	1))	
1. ℃	/)	
)	, +))	
	1)	



+.

	+.		1))	
	+.		1))	
	+.		2))	
	+.		2))	
	1.		/)	
	(+ .) +. ℃		, +))	
+		+	. +))	+
	+	(	.)	(
	.) (		, /)) (,)))	
			-) +.	℃
			-) +.	℃

+ .

"

1)	
))	
/)	
))	
/)	
) 11	
. .	
+)	
+.)	
,))	

(

+ .

.					
/) 1 +	/) 1 +	+	0) ±)	/	0+

FIG.1: Power dissipation vs. on-state current (per thyristor or diode)

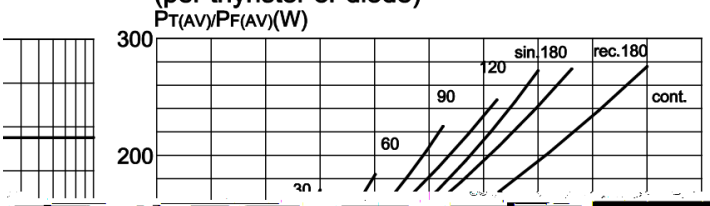


FIG.2: Maximum transient thermal impedance junction to case(per thyristor or diode)

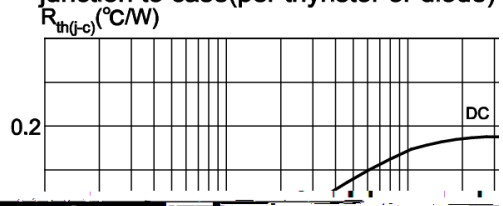


FIG.5 Gate trigger characteristics

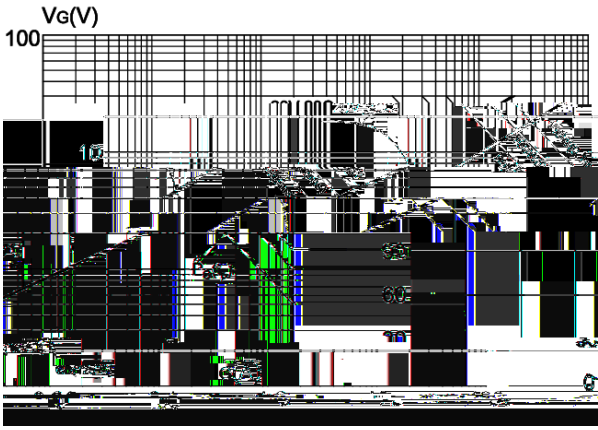
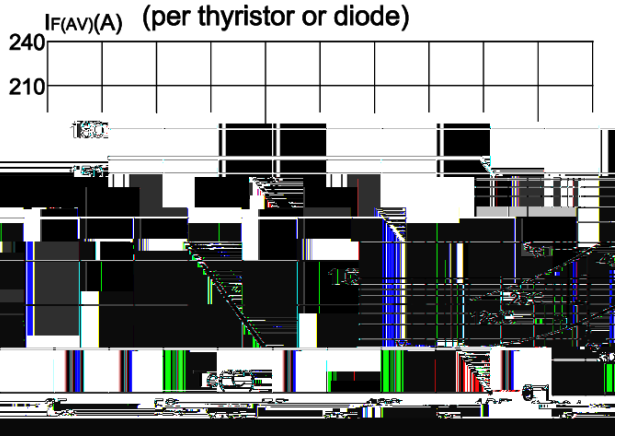
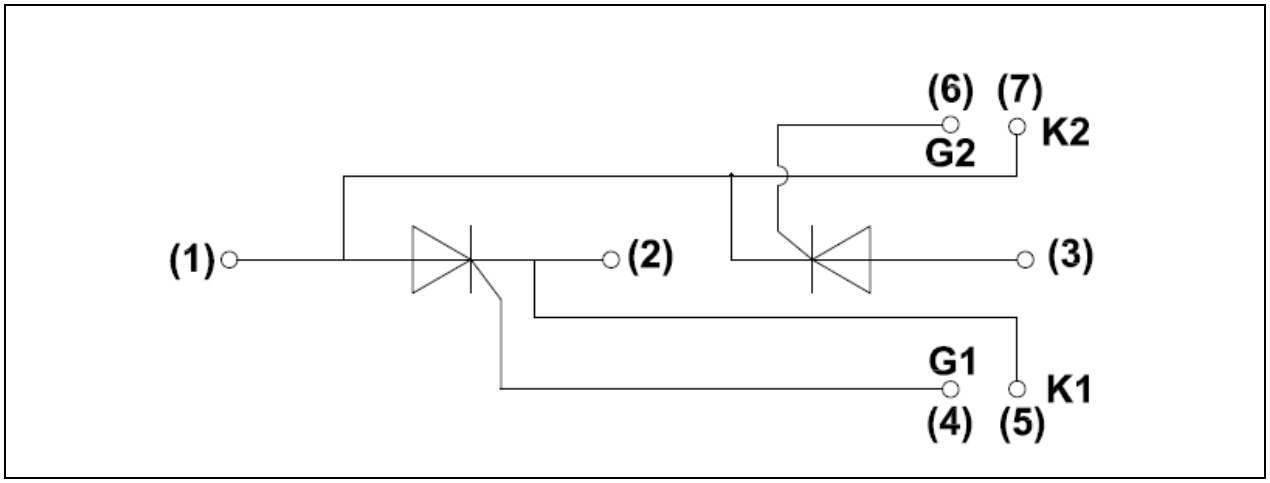
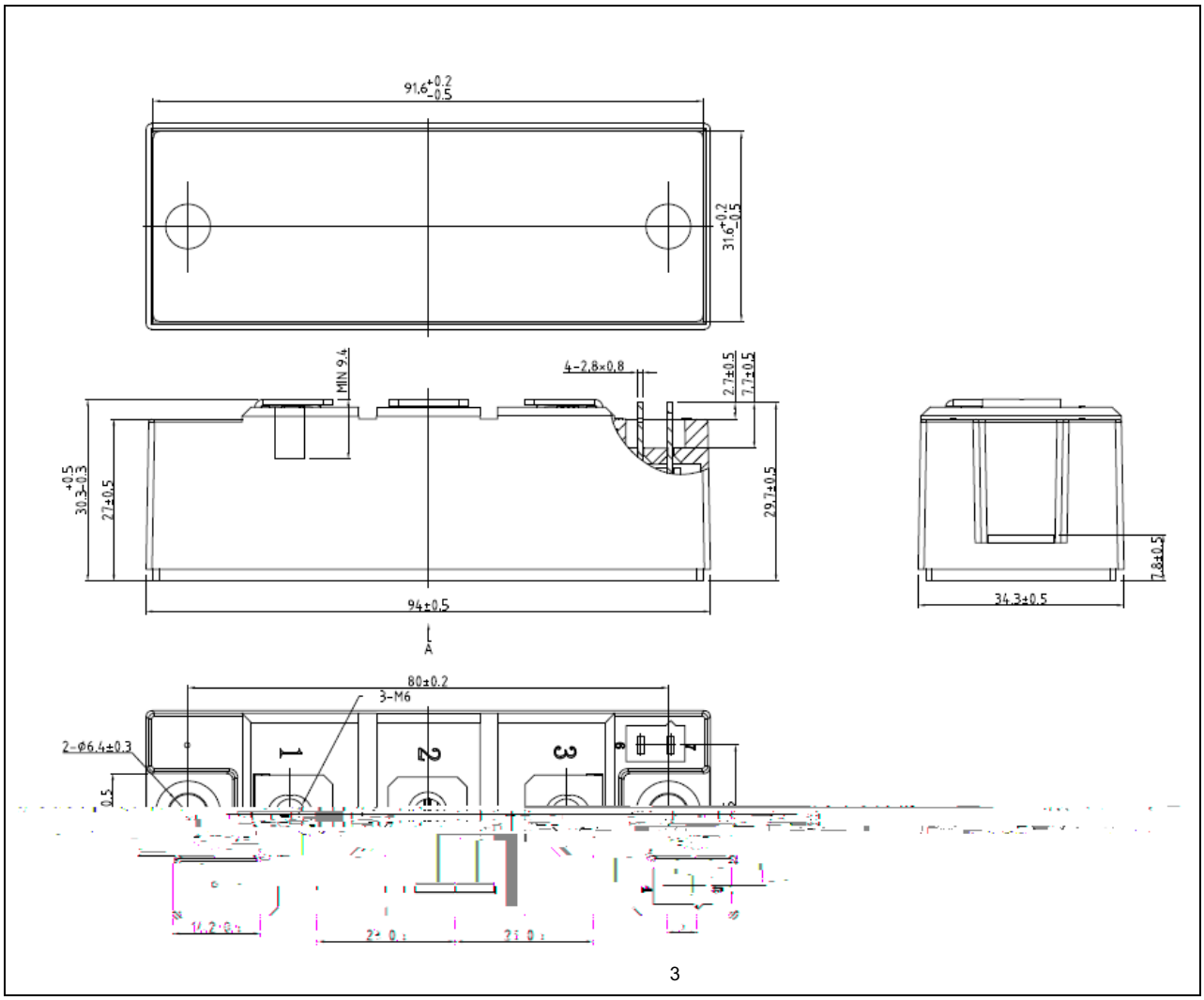


FIG.6: Forward current vs. case temperature (per thyristor or diode)



.


(6)
(7)
G2
K2
(1)
(2)
(3)
G1
K1
(4)
(5)


91,6+0.2 -0.5
31,6+0.2 -0.5
MIN 9.4
4-2,8×0,8
2.7±0.5
7.7±0.5
30.3+0.5 -0.3
27±0.5
29.7±0.5
94±0.5
7.8±0.5
34.3±0.5
A
80±0.2
3-M6
2-Φ6.4±0.3
0.5
1
2
3

- +) +/

+) +/

+